

TURBOSWITCH ™ "A". ULTRA-FAST HIGH VOLTAGE DIODE

MAIN PRODUCT CHARACTERISTICS

lf(av)	25A
V _{RRM}	1200V
t rr (typ)	60ns
V _F (max)	1.9V

FEATURES AND BENEFITS

- ULTRA-FAST, SOFT AND NOISE-FREE RECOVERY.
- VERY LOW OVERALL POWER LOSSES IN BOTH THE DIODE AND THE COMPANION TRANSISTOR.
- HIGH FREQUENCY AND/OR HIGH PULSED CURRENT OPERATIONS.
- CECC APPROVED.

DESCRIPTION

The TURBOSWITCH is a very high performance series of ultra-fast high voltage power diodes from 600V to 1200V.

TURBOSWITCH 1200V drastically cuts losses in all high voltage operations which require extremely fast, soft and noise-free power diodes. Due to their optimized switching performances they also highly decrease power losses in any associated switching IGBT or MOSFET in all "Freewheel

ABSOLUTE MAXIMUM RATINGS

Mode" operations.

They are particularly suitable in Motor Control circuitries, or in the primary of SMPS as snubber, clamping or demagnetizing diodes, and also at the secondary of SMPS as high voltage rectifier diodes.

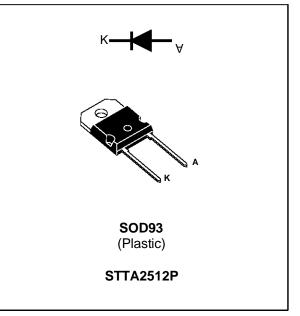
Packaged in SOD93, this 1200V device is particularly intended for use on 3 phase 400V industrial mains.

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	1200	V
Vrsm	Non repetitive peak reverse voltage	1200	V
I _{F(RMS)}	RMS forward current	50	А
I _{FRM}	Repetitive peak forward current (tp = 5 μ s, f = 5kHz)	300	А
Tj	Max operating junction temperature	150	°C
T _{stg}	Storage temperature	-65 to 150	°C

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PRELIMINARY DATA



THERMAL AND POWER DATA

Symbol	Parameter	Conditions	Value	Unit
R _{th(j-c)}	Junction to case thermal resistance		1.2	°C/W
P ₁	Conduction power dissipation (see fig. 6)	I _{F(AV)} = 25A δ =0.5 Tc= 82℃	57	W
P _{max}	Total power dissipation Pmax = P1 + P3 (P3 = 10% P1)	Tc= 75℃	62.5	W

STATIC ELECTRICAL CHARACTERISTICS (see Fig.6)

Symbo	bl	Parameter	Test C	Conditions	Min	Тур	Max	Unit
VF	*	Forward voltage drop	I _F =25A	Tj = 25℃ Tj = 125℃			2.1 1.9	>
I _R *	**	Reverse leakage current	V _R =0.8 x V _{RRM}	Tj = 25℃ Tj = 125℃			150 8.0	μA mA

Test pulses widths : * tp = 380 μ s, duty cycle < 2% ** tp = 5 ms , duty cycle < 2%

DYNAMIC ELECTRICAL CHARACTERISTICS

TURN-OFF SWITCHING (see Fig.7)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
trr	Reverse recovery time	$ Tj = 25^{\circ}C \\ I_F = 0.5 \text{ A } I_R = 1 \text{ A } Irr = 0.25 \text{ A } \\ I_F = 1 \text{ A } dI_F/dt = -50 \text{ A}/\mu \text{ s } V_R = 30 \text{ V } $		60	110	ns
I _{RM}	Maximum reverse recovery current	Tj = 125°C VR = 600V I _F =25A dI _F /dt = -200 A/μs dI _F /dt = -500 A/μs		TBD	TBD	A
S factor	Softness factor	Tj = 125°C V _R = 600V I _F =25A dI _F /dt = -500 A/μs		1.2		/

TURN-ON SWITCHING (see Fig.8)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
t _{fr}	Forward recovery time	Tj = 25°C I _F =25 A, dI _F /dt = 200 A/ μ s measured at, 1.1 × V _F max			TBD	ns
V _{Fp}	Peak forward voltage	Tj = 25°C I _F =25A, dI _F /dt = 200 A/μs I _F =40A, dI _F /dt = 500 A/μs			TBD TBD	V



APPLICATION DATA

The 1200V TURBOSWITCH series has been designed to provide the lowest overall power losses in all high frequency or high pulsed current operations. In such applications (Fig 1 to 5),the way of calculating the power losses is given below :

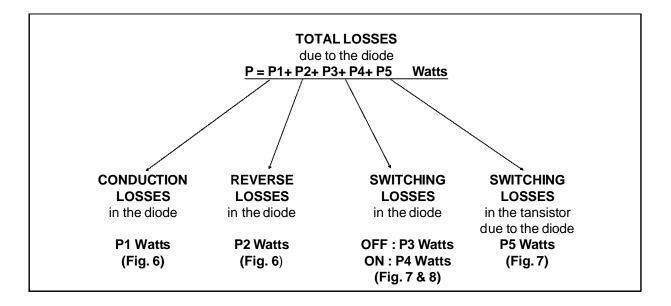


Fig. 1 : "FREEWHEEL" MODE.

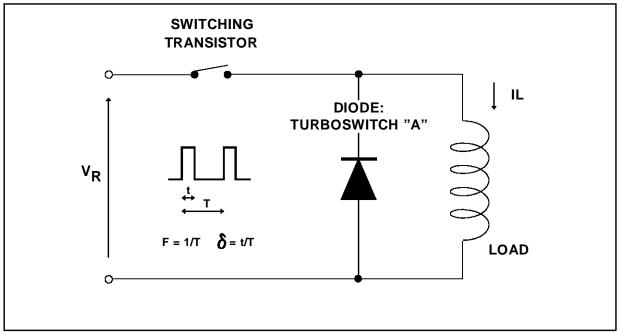




Fig. 2: SNUBBER DIODE.

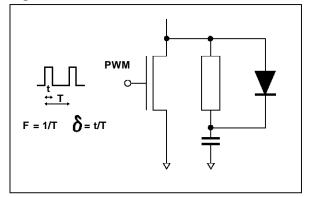


Fig. 4 : DEMAGNETIZING DIODE.

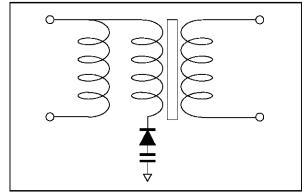


Fig. 3 : CLAMPING DIODE.

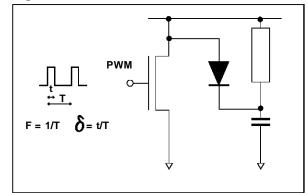
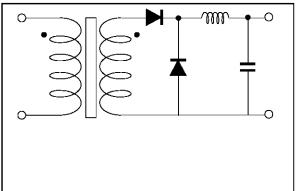
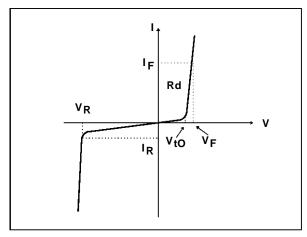


Fig. 5 : RECTIFIER DIODE.



STATIC & DYNAMIC CHARACTERISTICS . POWER LOSSES .

Fig. 6: STATIC CHARACTERISTICS



Conduction losses :

 $P1 = V_{t0} \cdot I_{F}(AV) + R_{d} \cdot I_{F}^{2}(RMS)$

with

 $\label{eq:Vt0} \begin{array}{l} V_{t0} = 1.52 \ V \\ R_d = 0.015 \ Ohm \\ (Max \ values \ at \ 125 ^\circ C, suitable \ for \ Ipeak < 3.I_{F(av)} \) \end{array}$

Reverse losses :

 $P2 = V_R \cdot I_R \cdot (1 - \delta)$



APPLICATION DATA (Cont'd)

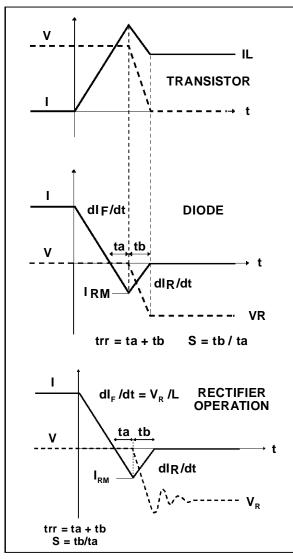
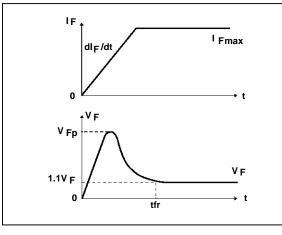


Fig. 7: TURN-OFF CHARACTERISTICS





Turn-on losses : (in the transistor, due to the diode)

$$P5 = \frac{V_R \times I_{RM}^2 \times (3 + 2 \times S) \times F}{6 x \, dI_F / dt} + \frac{V_R \times I_{RM} \times I_L \times (S + 2) \times F}{2 x \, dI_F / dt}$$

Turn-off losses (in the diode) :

$$P3 = \frac{V_R \times I_{RM}^2 \times S \times F}{6 x \, dI_F / dt}$$

Turn-off losses : (with non negligible serial inductance)

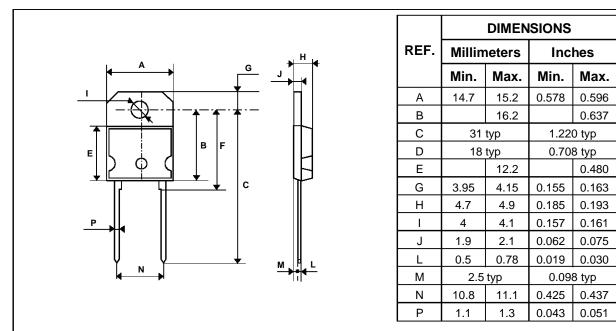
$$P3' = \frac{V_R \times I_{RM}^2 \times S \times F}{6 \times dI_F/dt} + \frac{L \times I_{RM}^2 \times F}{2}$$

P3,P3' and P5 are suitable for power MOSFET and IGBT

Turn-on losses : $P4 = 0.4 (V_{FP} - V_F) \cdot I_{Fmax} \cdot t_{fr} \cdot F$



PACKAGE MECHANICAL DATA SOD93



Cooling method : C Marking : Type number Weight : 5.2 g Recommended torque value : 0.8m.N Maximum torque value : 1.0m.N

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